DESCRIPTION

INFRARED EMITTING DIODE

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#### **■** Features

- · Narrow beam angle
- Durable
- High reliability in demanding environments

## Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol Rating		Unit	
Forward Current	IF.	100	mΛ	
Pulse Forward Current	IFP	1	A	
Reverse Voltage	VR	5	V	
Power Dissipation	PD	200	- mW	
Operating Temperature	Topr	-40 ~ +100	°C	
Storage Temperature	Tstg	-55 ~ +125	°C	

# ■ Electro-Optical Characteristics

(Ta=25°C)

Parameter	. Symbol	Test.Condition	Min-	- Typ -	Max	Unit
Forward Voltage	VF	IF=100mA		1.35	1.7	V
Reverse Current	IR	VR=5V			10	μA.
Output Power	PO	IF=100mA		15		nW/Sr
Terminal Capacitance	Ct	f=1 Miz		25	-	pF
Angle Sensitivity at 50%	θ			±8		deg
Peak Emittion Wavelength	λp	IF=60m/		940		nm
Spectral Bandwidth at 50%	Δλ	IF=60mA		50		nm

### DESCRIPTION

DEVICE

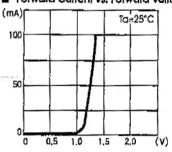
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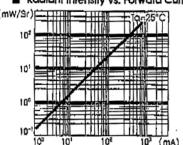
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INFRARED EMITTING DIODE

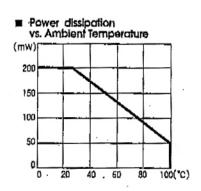
KID-05AC94

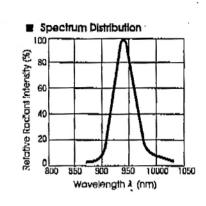
■ Forward Current vs. Forward Voltage ■ Radiant Intensity vs. Forward Current

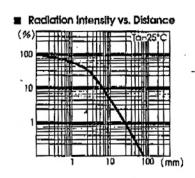




Relative Radiant Intensity
vs. Ambient Temperature







### Radiation Diagram

